

GaAs MMIC VSAT Power Amplifier, 1.4W 14.0 - 14.5 GHz



Features

- High Linear Gain: 22 dB Typ.
- High Saturated Output Power: +31.5 dBm Typ.
- High Power Added Efficiency: 22% Typ.
- 50Ω Input/Output Broadband Matched
- Integrated Output Power Detector
- High Performance Ceramic Bolt Down Package

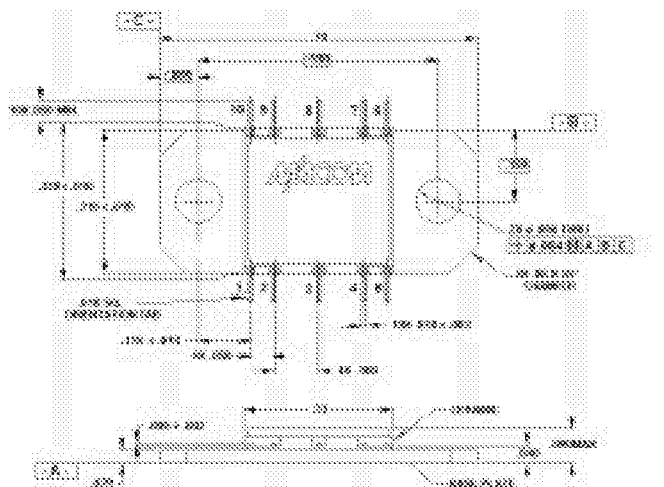
Description

MA-COM's AM42-0002 is a three-stage MMIC linear power amplifier in a ceramic bolt down style hermetic package. The AM42-0002 employs a fully matched chip with internally decoupled Gate and Drain bias networks and an output power detector. The AM42-0002 is designed to be operated from a constant voltage Drain supply.

The AM42-0002 is designed for use as an output stage or a driver, in applications for VSAT systems. This design is fully monolithic and requires a minimum of external components.

M/A-COM's AM42-0002 is fabricated using a mature 0.5 micron GaAs MESFET process. The process features full passivation for increased performance and reliability. This product is 100% RF tested to ensure compliance to performance specifications.

CR-15



Notes: (unless otherwise specified)

1. Dimensions are in inches.
2. Tolerance: .XXX = ± 0.005
 XX = ± 0.010

Ordering Information

Part Number	Package
AM42-0002	Ceramic Bolt Down Package

Electrical Specifications: $T_c = +25^{\circ}\text{C}$, $V_{DD} = +9\text{V}$, $V_{GG} = -5.0\text{V}$, $Z_0 = 50\Omega$, Frequency = 14.0-14.5 GHz

Parameter	Abbv.	Test Conditions	Units	Min.	Typ.	Max.
Linear Gain	G_L	$P_{IN} \leq 0$ dBm	dB	19	22	—
Input VSWR	$VSWR_{IN}$	$P_{IN} \leq 0$ dBm	—	—	2.5:1	2.7:1
Output VSWR	$VSWR_{OUT}$	—	—	—	2.7:1	—
Saturated Output Power	P_{SAT}	$P_{IN} = +14$ dBm	dBm	30.5	31.5	—
Output Power @ 1 dB Compression	P_{1dB}		dBm	—	29.5	—
Output Third Order Intercept	IP_3	(Refer to Note 1)	dBm	—	41	—
Power Added Efficiency	PAE	$P_{IN} = +14$ dBm	%	—	22	—
Bias Currents	I_{DD}	$P_{IN} = +14$ dBm	mA	—	950	1400
	I_{GG}	$P_{IN} = +14$ dBm	mA	—	18	25
Thermal Resistance	θ_{JC}	25°C Heat Sink	°C/W	—	9.5	—
Detector Output Voltage	V_{det}	$R_L = 10K\Omega$ min. $P_{IN} = +14$ dBm	V	—	+3.5	—

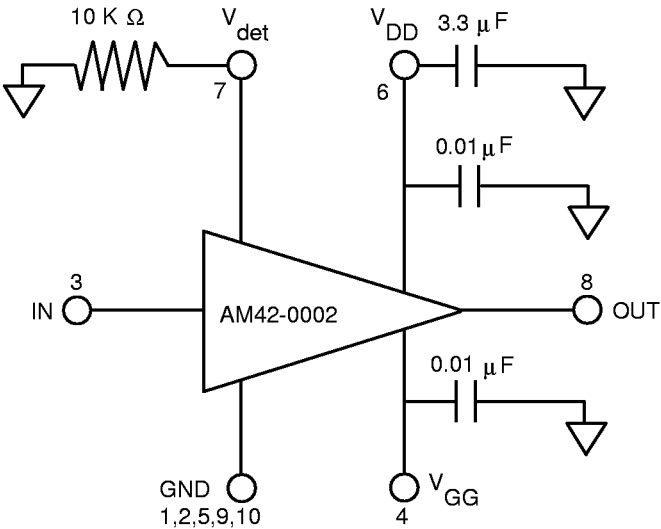
IP₃ is measured with two +21 dBm output tones @ 1 MHz spacing.

Absolute Maximum Ratings^{1,2,3,4}

Parameter	Absolute Maximum
V _{DD}	12 Volts
V _{GG}	-10 Volts
Power Dissipation	13.2 W
RF Input Power	+23 dBm
Channel Temperature	150°C
Storage Temperature	-65°C to +150°C
I _{ds}	1900 mA

- 1. Operation of this device outside any of these limits may cause permanent damage.
- 2. Case Temperature (T_C) = +25°C.
- 3. Nominal bias is obtained by first connecting -5 volts to pin 4 (V_{GG}), followed by connection +9 volts to pin 6 (V_{DD}). Note sequence.
- 4. RF ground and thermal interface is the flange (case bottom). Adequate heat sinking is required.
- 5. No dc bias voltage appears at the RF ports.
- 6. The dc resistance at the input port is an open circuit and at the output port is a short circuit.
- 7. For optimum IP₃ performance, the V_{DD} bypass capacitors should be placed within 0.5 inches of pin 6.
- 8. Resistor and capacitors surrounding the amplifier are suggestions and not included as part of the AM42-0002.

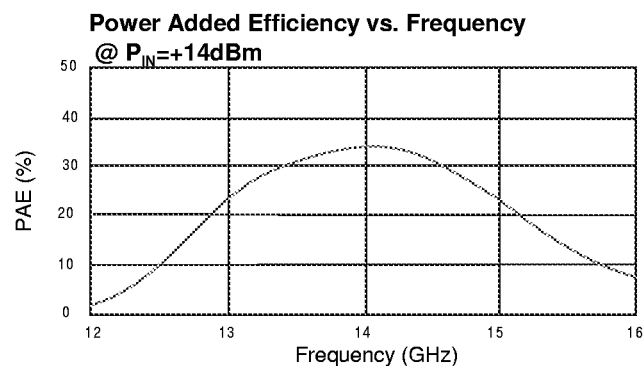
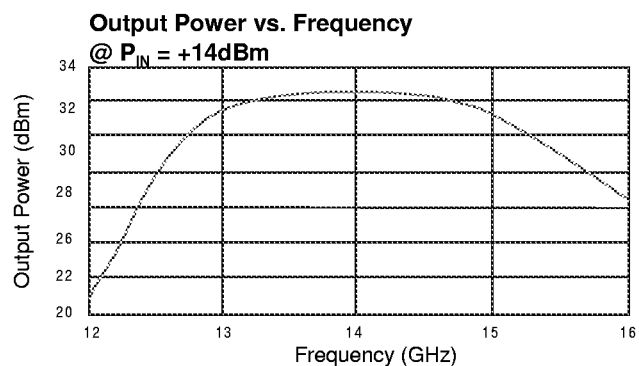
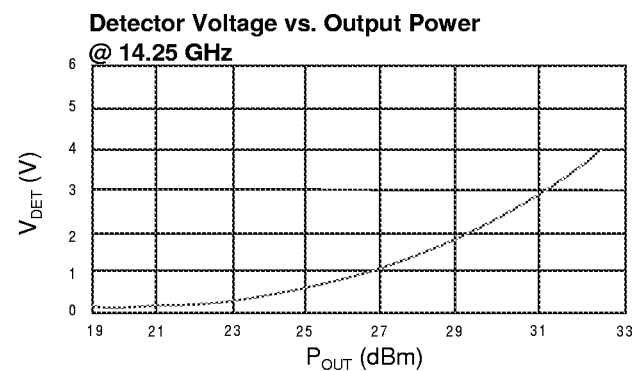
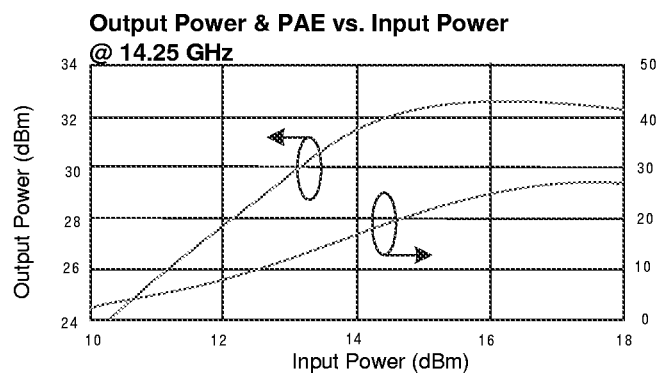
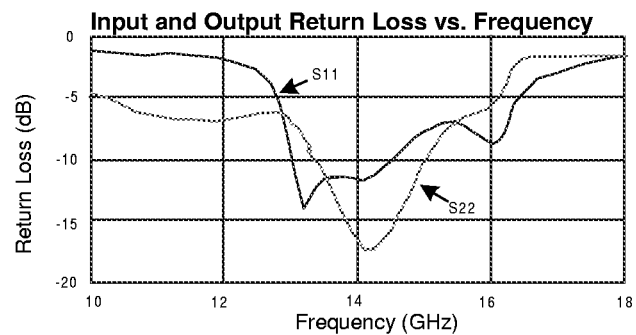
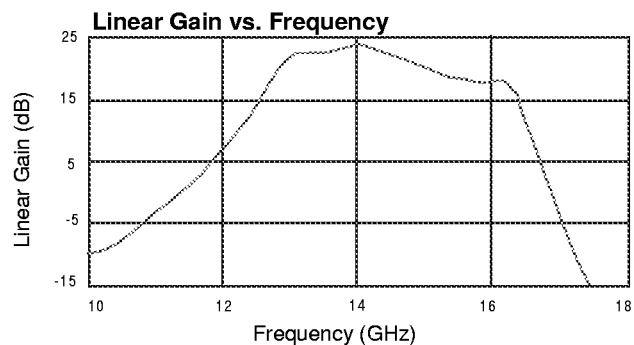
Typical Bias Configuration^{3,4,7,8}



Pin No.	Pin Name	Description
1	GND	DC and RF Ground
2	GND	DC and RF Ground
3	IN	RF Input
4	V _{GG}	Gate Supply
5	GND	DC and RF Ground
6	V _{DD}	Voltage Drain Supply
7	V _{det}	Output Power Detector
8	OUT	RF Output
9	GND	DC and RF Ground
10	GND	DC and RF Ground

Typical Performance @ +25 °C

Test Conditions are listed in the section “Electrical Specifications”.



V3.00